In the Claims:

Please amend the claims as follows:

What is claimed is:

1. (Twice Amended) A semiconductor laser device comprising:

- a semiconductor laser element with at least one exit surface from which laser light can emerge, which in a first direction (Y) has greater divergence than in a second direction which is perpendicular to it;

- at least one reflection means which is located spaced apart from the exit surface outside of the semiconductor laser element, with a reflecting surface which can reflect back at least parts of the light which has emerged from the semiconductor laser element through the exit surface into the semiconductor laser element such that a mode spectrum of the semiconductor laser element is influenced thereby;

- and a lens means which is located between the reflection means and the semiconductor laser element and which can at least partially reduce the divergence of the laser light at least in the first direction (Y),

wherein

- the reflecting surface of the reflection means is concavely curved ~~or spherically curved~~.

2. (Cancelled)

3. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the reflecting surface in the first direction (Y) and in the second direction which is perpendicular to it has a curvature of essentially the same size or curvatures of differing magnitude.

4. (Cancelled)

5. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein an optical distance (D) between the reflecting surface and the exit surface of the semiconductor laser element is essentially equal to the focal length (F) of the reflecting surface with respect to at least one of the directions (Y).

6. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the exit surface of the semiconductor laser element facing the reflection means has a width of more than 200 microns and the reflecting surface is not curved or is curved only insignificantly.

7. (Previously Amended) The semiconductor laser device as claimed in claim 6, wherein the exit surface has a width of more than 500 microns, or more than 1 mm.

8. (Previously Amended) The semiconductor laser device as claimed in claim 6, wherein the reflecting surface or at least one of the reflecting surfaces is made as a wavelength-sensitive element, or as a grating.

9. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the optical distance (D) and/or the curvature of the reflecting surface are chosen such that the beam waist on the exit surface of at least component beams of the light which has been reflected back to the semiconductor laser element corresponds essentially to an aperture which is formed by the exit surface.

10. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser element is a broad strip emitter or a bar or stack of broad strip emitters.

11. (Cancelled)

12. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the exit surface of the semiconductor laser element facing the reflecting surface is coated with an antireflective coating.

13. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser device

comprises two reflection means with two reflecting surfaces, the two reflecting surfaces each being tilted at oppositely equal angles (α) to the normal on the exit surface.

14. (Previously Amended) The semiconductor laser device as claimed in claim 13, wherein the two reflecting surfaces of the two reflection means have a same optical distance (D) to the exit surface of the semiconductor laser element.

15. (Previously Amended) The semiconductor laser device as claimed in claim 13, wherein at least one of the two reflecting surfaces of the two reflection means is made as a partially reflecting surface so that at least one reflection means which is provided with a partially reflecting surface is used as a decoupler.

16. (Twice Amended) The semiconductor laser device as claimed in claim 13, wherein the two reflecting surfaces of the reflection means are made highly reflecting, the exit surface of the semiconductor laser element ~~(1)~~ facing away from the reflecting surfaces being made partially reflecting and being used as a decoupler in this way.

17. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein between the semiconductor laser element and the at least one reflection means there is a deflection means which can deflect onto the at least one reflection means the

component beams which are emerging at an angle (α) to the normal on the exit surface from the latter.

18. (Previously Amended) The semiconductor laser device as claimed in claim 17, wherein the deflection means and the at least one reflection means are located on an axis which is dictated by a middle perpendicular on the exit surface.

19. (Previously Amended) The semiconductor laser device as claimed in claim 17, wherein the deflection means is as a prism element.

20. (Previously Amended) The semiconductor laser device as claimed in claim 19, wherein the prism element is arranged such that the leg surfaces are facing the exit surface of the semiconductor element.

21. (Previously Amended) The semiconductor laser device as claimed in claim 20, wherein by the suitable choice of the angle (β) between a hypotenuse surface and the leg surfaces of the prism element and/or by the suitable choice of the position of the prism element between the exit surface and the reflecting surface component beams which emerge at an angle ($\pm \alpha$) relative to the normal on the exit surface from the latter can be transferred into one another by the reflecting surface of the at least one reflection means.

22. (Previously Amended) The semiconductor laser device as claimed in claim 17, wherein the reflecting surface of the at least one reflection means is made partially reflective so that the at least one reflection means can be used as a decoupler.

23. (Previously Amended) The semiconductor laser device as claimed in claim 17, wherein the reflecting surface of the at least one reflection means is made highly reflecting, the exit surface of the semiconductor laser element facing away from the reflecting surface being made partially reflecting and in this way being able to be used as a decoupler.

24. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein between the semiconductor laser element and the at least one reflection means there is a wavelength-selective element which is an etalon.

25. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the lens means is made as a cylinder lens with a cylinder axis which extends essentially in the second direction which is perpendicular to the first direction (Y), or is made such that the laser light which has emerged from the exit surface of the passing through the lens means in the first direction (Y) has a divergence roughly the same magnitude as in the second direction which is perpendicular thereto.

26. (Cancelled)

27. (Previously Amended) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser element is exposed to a voltage and is supplied with a current for producing electron-hole pairs only in partial areas which correspond to a three-dimensional extension of the desired mode of the laser light.

28. (New) The semiconductor laser device as claimed in claim 1, wherein the reflecting surface is spherically curved.